CHANGE NOTIFICATION

Analog Devices, Inc.
1630 McCarthy Blvd., Milpitas CA
(408) 432-1900

August 06, 2018 PCN#080618

Dear Sir/Madam:

Subject: Notification of Change to LTC4362-1, LTC4362-2 Datasheet

Please be advised that Analog Devices, Inc. Milpitas, California has made a minor change to the LTC4362-1, LTC4362-2 product datasheet to facilitate improvement in our manufacturing capability. The changes are shown on the attached page of the marked up datasheet. There was no change in form, fit, function, quality or reliability of the product. The product shipped after October 06, 2018 will be tested to the new limits.

Should you have any questions or concerns please contact your local Analog Devices sales representatives or you may contact me at 408-432-1900 ext. 2077, or by e-mail at JASON.HU@ANALOG.COM. If I do not hear from you by October 06, 2018, we will consider this change to be approved by your company.

Sincerely,

Jason Hu
Quality Assurance Engineer

For questions on this PCN, please contact Jason Hu or you may send an email to your regional contacts below or contact your local ADI sales representatives.			
Americas: PCN_Americas@analog.com	**Europe:** PCN_Europe@analog.com	**Japan:**	PCN_Japan@analog.com
		Rest of Asia:	PCN_ROA@analog.com

new parameter

ELECTRICAL CHARACTERISTICS

The ● denotes the specifications which apply over the full operating temperature range, otherwise specifications are at T_A = 25°C. V_{IN} = 5V, $V_{\overline{ON}}$ = 0V unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS
Supplies							
V_{IN}	Input Voltage Range		●	2.5		28	V
$V_{IN(UVL)}$	Input Undervoltage Lockout	V_{IN} Rising	●	1.8	2.1	2.45	V
I_{IN}	Input Supply Current	$V_{\overline{ON}}$ = 0V $V_{\overline{ON}}$ = 2.5V	● ●		220 1.5	400 10	µA µA
Thresholds							
$V_{IN(OV)}$	IN Pin Overvoltage Threshold	V_{IN} Rising	●	5.684	5.8	5.916	V
$V_{IN(OVL)}$	IN Pin Overvoltage Recovery Threshold	V_{IN} Falling	●	5.51	5.7	5.85	V
ΔV_{OV}	Overvoltage Hysteresis		●	25	100	~~200~~ 300	mV
Input Pins							
$V_{\overline{ON}(TH)}$	$\overline{ON}$ Input Threshold		●	0.4		1.5	V
$I_{\overline{ON}}$	$\overline{ON}$ Pull-Down Current	$V_{\overline{ON}}$ = 2.5V	●	2.5	5	10	µA
Output Pins							
$V_{OUT(UP)}$	OUT Turn-On Ramp-Rate	V_{OUT} = 0.5V to 4V	●	1.5	3	4.5	V/ms
I_{OUT}	OUT Leakage Current	$V_{\overline{ON}}$ = 2.5V, V_{OUT} = 5V	●		0	±3	µA
$V_{GATEP(CLP)}$	IN to GATEP Clamp Voltage	V_{IN} = 8V to 28V	●	5	5.8	7.5	V
R_{GATEP}	GATEP Pull-Down Resistance	V_{GATEP} = 3V	●	0.8	2	3.2	MΩ
$V_{\overline{PWRGD}(OL)}$	$\overline{PWRGD}$ Output Low Voltage	V_{IN} = 5V, $I_{\overline{PWRGD}}$ = 3mA	●		0.23	0.4	V
$R_{\overline{PWRGD}}$	$\overline{PWRGD}$ Pull-Up Resistance to OUT	V_{IN} = 6.5V, $V_{\overline{PWRGD}}$ = 1V	●	250	500	800	kΩ
Internal N-Channel MOSFET							
R_{ON}	On Resistance	I_{OUT} = 0.5A	●		40	70	mΩ
I_{TRIP}	Overcurrent Threshold		●	1.2	1.5	1.8	A
I_{AS}	Peak Avalanche Current	L = 0.1mH (Note 5)			10		A
E_{AS}	Single Pulse Avalanche Energy	I_{AS} = 10A, L = 0.1mH (Note 5)			10		mJ
Delay							
t_{ON}	Turn-On Delay	V_{IN} High to V_{OUT} = 0.5V, R_{OUT} = 1kΩ	●	50	130	200	ms
$t_{OFF(OV)}$	Turn-Off Delay for Overvoltage	V_{IN} = 5V ⌐ 6.5V to V_{OUT} = 4.5V, R_{OUT} = 1kΩ	●		0.45	1	µs
$t_{OFF(OC)}$	Turn-Off Delay for Overcurrent	I_{OUT} = 0.5A ⌐ 3A to V_{OUT} = 4.5V	●	5	10	20	µs
$t_{\overline{PWRGD}(LH)}$	$\overline{PWRGD}$ Rising Delay	V_{IN} = 5V ⌐ 6.5V to $\overline{PWRGD}$ High	●		0.3	1	µs
$t_{\overline{PWRGD}(HL)}$	$\overline{PWRGD}$ Falling Delay	V_{IN} = 0V ⌐ 5V, V_{OUT} = 0.5V to $\overline{PWRGD}$ Low, R_{OUT} = 1kΩ	●	25	65	100	ms
$t_{\overline{ON}(OFF)}$	$\overline{ON}$ High to N-channel MOSFET Off	$V_{\overline{ON}}$ = 0V ⌐ 2.5V	●		40	100	µs
ESD Protection							
	ESD Protection for IN to GND	C_{OUT} = 1µF, Human Body Model			±25		kV

Note 1: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

Note 2: All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to GND unless otherwise specified.

Note 3: The minimum drain-source breakdown voltage of the internal MOSFET is 28V. Driving the IN and SENSE pins more than 28V above OUT may damage the device if the E_{AS} capability of the MOSFET is exceeded.

Note 4: An internal current sense resistor ties IN and SENSE. Driving SENSE relative to IN may damage the resistor.

Note 5: The I_{AS} and E_{AS} typical values are based on characterization and are not production tested.